

**LISTING OF THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (Canceled)

6. (Previously Presented) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion, wherein the second crystalline portion is a region where a metal was directly added, and

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion.

7-13. (Canceled)

14. (Previously Presented) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion,

wherein the second crystalline portion has a surface through which a metal is added, and

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion.

15. (Previously Presented) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion,

wherein the second crystalline portion is a region where a metal was directly added,

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion, and

wherein a crystal of the first crystalline portion is a crystal which grew in a horizontal direction from the second crystalline portion.

16. (Previously Presented) A transistor comprising:

a channel region; and

at least one of a source region and a drain region having a first crystalline portion adjacent to the channel region and a second crystalline portion adjacent to the first crystalline portion,

wherein the second crystalline portion has a surface through which a metal is added, and

wherein the first crystalline portion is a region where crystallization advanced from the second crystalline portion, and

wherein a crystal of the first crystalline portion is a crystal which grew in a horizontal direction from the second crystalline portion.

17. (Canceled)

18. (Previously Presented) The transistor according to claim 6, further comprising a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,

wherein the gate insulating film has an opening overlapping with the second crystalline portion.

19. (Previously Presented) The transistor according to claim 6,  
wherein the metal is nickel.

20. (Previously Presented) The transistor according to claim 6,  
wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium.

21. (Canceled)

22. (Previously Presented) The transistor according to claim 14, further comprising

a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,

wherein the gate insulating film has an opening overlapping with the second crystalline portion.

23. (Previously Presented) The transistor according to claim 14,  
wherein the metal is nickel.

24. (Previously Presented) The transistor according to claim 14,  
wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium.

25. (Canceled)

26. (Previously Presented) The transistor according to claim 15, further comprising  
a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,  
wherein the gate insulating film has an opening overlapping with the second crystalline portion.

27. (Previously Presented) The transistor according to claim 15,  
wherein the metal is nickel.

28. (Previously Presented) The transistor according to claim 15,  
wherein the metal is at least one from the group consisting of nickel, iron, cobalt, platinum, and palladium.

29. (Canceled)

30. (Previously Presented) The transistor according to claim 16, further comprising  
a gate insulating film over the channel region, the first crystalline portion, and the second crystalline portion,  
wherein the gate insulating film has an opening overlapping with the second crystalline portion.

31. (Previously Presented) The transistor according to claim 16,  
wherein the metal is nickel.

32. (Previously Presented) The transistor according to claim 16,  
wherein the metal is at least one from the group consisting of nickel, iron, cobalt,  
platinum, and palladium.